

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3400X uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

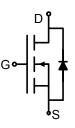
• $V_{DS} = 30V, I_D = 5.1A$

 $R_{DS(ON)}$ < 55m Ω @ V_{GS} =2.5V

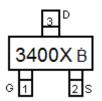
 $R_{DS(ON)}$ < 39m Ω @ V_{GS} =4.5V

 $R_{DS(ON)}$ < 33m Ω @ V_{GS} =10V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3400X B	NCE3400X	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous	I _D	5.1	Α
Drain Current-Pulsed (Note 1)	I _{DM}	20	Α
Maximum Power Dissipation	P _D	1.3	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	ReJA	96	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μΑ



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NCE3400X

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	•					
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.7	0.9	1.2	V
	R _{DS(ON)}	V_{GS} =2.5V, I_D =3A	-	33	55	mΩ
rain-Source On-State Resistance		V _{GS} =4.5V, I _D =4A	-	26	39	mΩ
		V _{GS} =10V, I _D =5A	-	24	33	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =5A	10	-	-	S
Dynamic Characteristics (Note4)	•					
Input Capacitance	C _{lss}	\/ =15\/\/ =0\/	-	595	-	PF
Output Capacitance	Coss	V_{DS} =15V, V_{GS} =0V, F=1.0MHz	-	39	-	PF
Reverse Transfer Capacitance	C _{rss}	F = 1.0Wil 12	-	36	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	3.0	-	nS
Turn-on Rise Time	t _r	V_{DD} =15V, R_L =3 Ω	-	4.5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =3 Ω	-	25	-	nS
Turn-Off Fall Time	t _f		-	3.8	-	nS
Total Gate Charge	Qg	V _{DS} =15V,I _D =5A,	-	9.3	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =4.5V	-	2.1	-	nC
Drain-Source Diode Characteristics	•					-
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =5A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	5.1	Α

Notes:

- Repetitive Rating: Pulse width limited by maximum junction temperature.
 Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

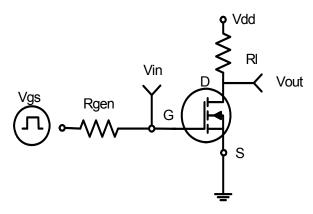
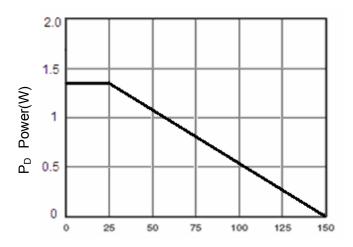


Figure 1:Switching Test Circuit



T_J-Junction Temperature(°C)

Figure 3 Power Dissipation

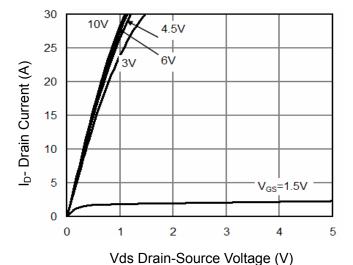


Figure 5 Output Characteristics

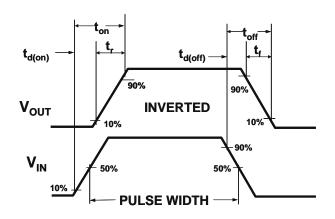


Figure 2:Switching Waveforms

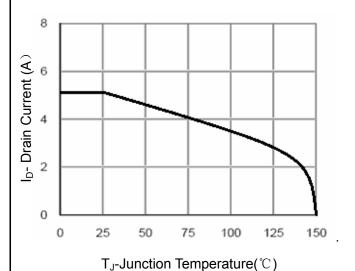


Figure 4 Drain Current

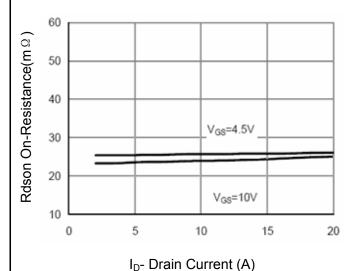
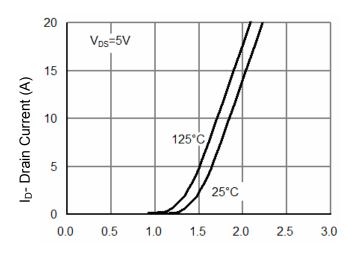


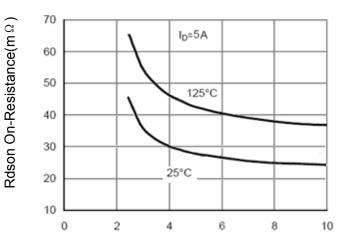
Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)

Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

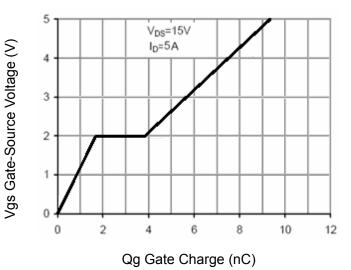
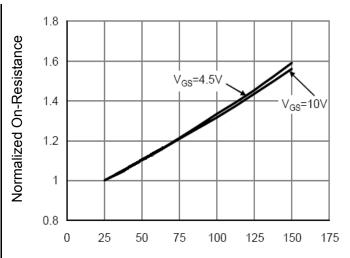


Figure 11 Gate Charge



 T_J -Junction Temperature($^{\circ}$ C)



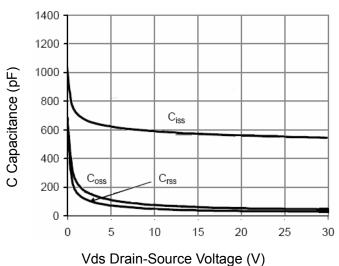


Figure 10 Capacitance vs Vds

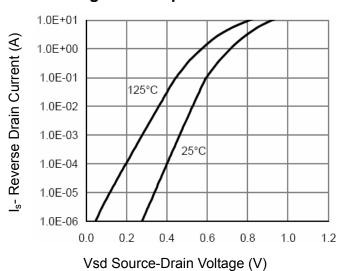
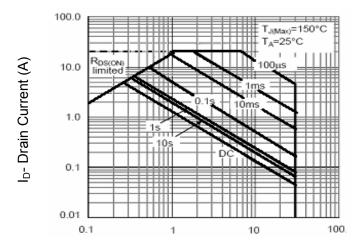


Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

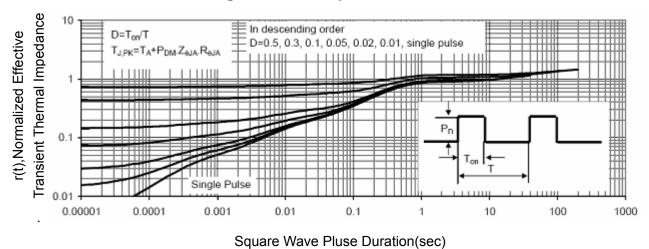
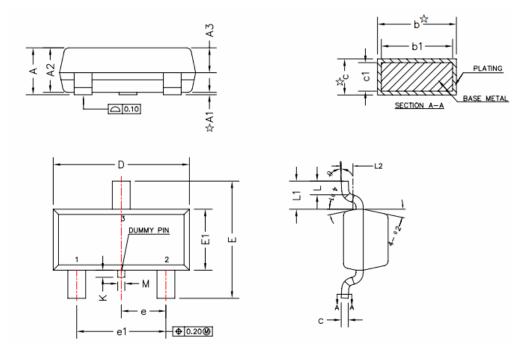


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Millimeters				
Syllibol	Min.	Max.			
Α	0.89	1.12			
A1	0.01	0.10			
A2	0.88	1.02			
A3	0.43	0.63			
b	0.36	0.50			
b1	0.35	0.45			
С	0.14	0.20			
c1	0.14	0.16			
D	2.80	3.00			
E	2.35	2.64			
E1	1.20	1.40			
е	0.90	1.00			
e1	1.80	2.00			
L	0.40	0.60			
L1	0.6REF				
L2	0.25BSC				
М	0.10	0.25			
K	0.00	0.25			
θ	0°	8°			
θ1	10°	14°			
θ2	10°	14°			



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